

# BC640-016G

## High Current Transistors

### PNP Silicon

#### Features

- This is a Pb-Free Device

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	-80	Vdc
Collector-Base Voltage	$V_{CBO}$	-80	Vdc
Emitter-Base Voltage	$V_{EBO}$	-5.0	Vdc
Collector Current - Continuous	$I_C$	-0.5	Adc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

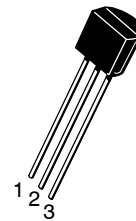
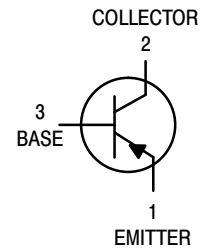
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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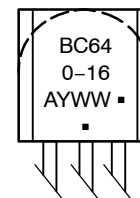
<http://onsemi.com>



TO-92  
CASE 29  
STYLE 14

STRAIGHT LEAD  
BULK PACK

#### MARKING DIAGRAMS



A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# BC640-016G

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = -10 mA, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	-80	-	-	Vdc
Collector – Base Breakdown Voltage (I <sub>C</sub> = -100 μA, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	-80	-	-	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = -10 μA, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	-5.0	-	-	Vdc
Collector Cutoff Current (V <sub>CB</sub> = -30 Vdc, I <sub>E</sub> = 0) (V <sub>CB</sub> = -30 Vdc, I <sub>E</sub> = 0, T <sub>A</sub> = 125°C)	I <sub>CBO</sub>	-	-	-100 -10	nA μA

## ON CHARACTERISTICS (Note 1)

DC Current Gain (I <sub>C</sub> = -5.0 mA, V <sub>CE</sub> = -2.0 Vdc) (I <sub>C</sub> = -150 mA, V <sub>CE</sub> = -2.0 Vdc) (I <sub>C</sub> = -500 mA, V <sub>CE</sub> = -2.0 V)	h <sub>FE</sub>	25 100 25	- - -	- 250 -	-
Collector – Emitter Saturation Voltage (I <sub>C</sub> = -500 mA, I <sub>B</sub> = -50 mA)	V <sub>CE(sat)</sub>	-	-0.25	-0.5	Vdc
Base – Emitter On Voltage (I <sub>C</sub> = -500 mA, V <sub>CE</sub> = -2.0 Vdc)	V <sub>BE(on)</sub>	-	-	-1.0	Vdc

## DYNAMIC CHARACTERISTICS

Current Gain – Bandwidth Product (I <sub>C</sub> = -50 mA, V <sub>CE</sub> = -2.0 Vdc, f = 100 MHz)	f <sub>T</sub>	-	150	-	MHz
Output Capacitance (V <sub>CB</sub> = -10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>ob</sub>	-	9.0	-	pF
Input Capacitance (V <sub>EB</sub> = -0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ib</sub>	-	110	-	pF

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle 2.0%.

## ORDERING INFORMATION

Device	Package	Shipping
BC640-016G	TO-92 (Pb-Free)	5000 Units / Bulk

# BC640-016G

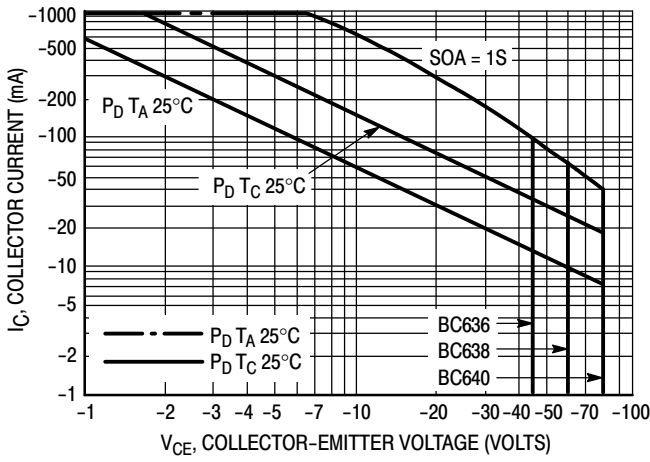


Figure 1. Active Region Safe Operating Area

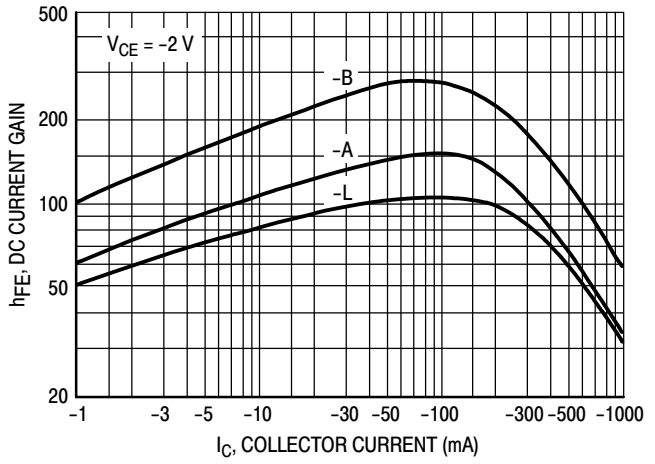


Figure 2. DC Current Gain

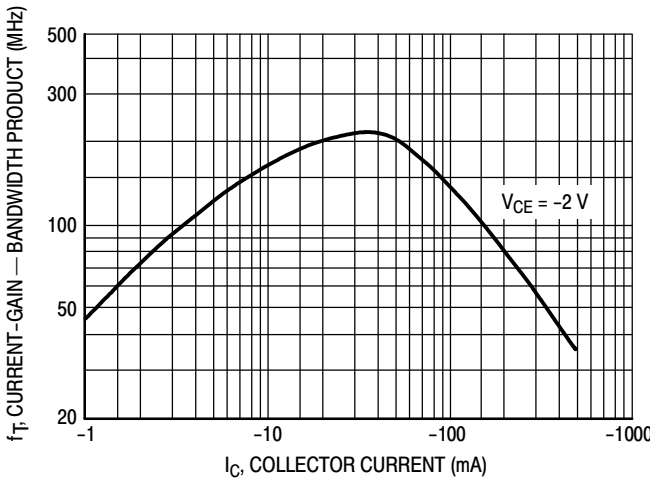


Figure 3. Current Gain Bandwidth Product

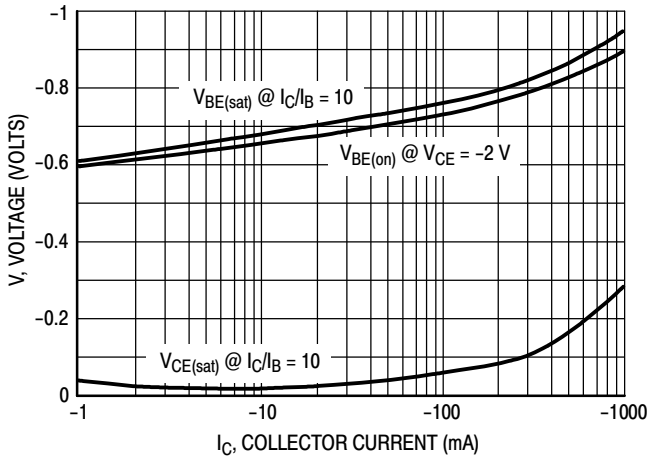


Figure 4. "Saturation" and "On" Voltages

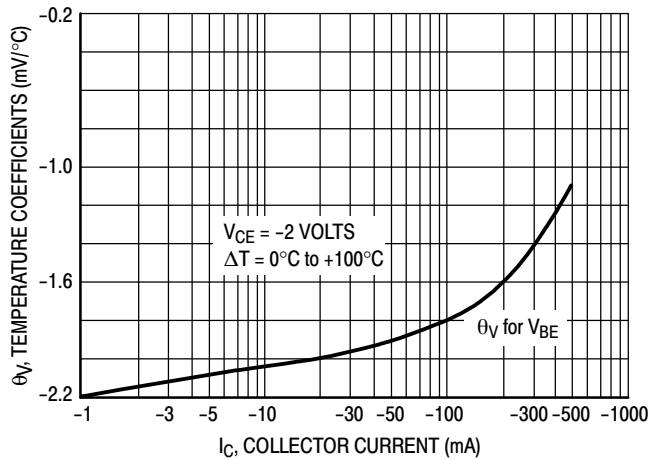
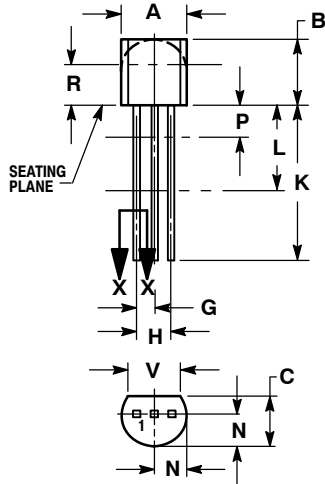


Figure 5. Temperature Coefficients

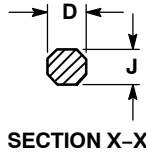
# BC640-016G

## PACKAGE DIMENSIONS

TO-92 (TO-226)  
CASE 29-11  
ISSUE AN



STRAIGHT LEAD  
BULK PACK

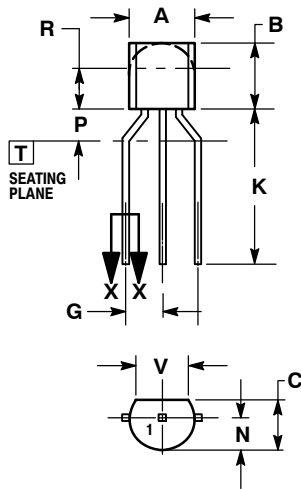


SECTION X-X

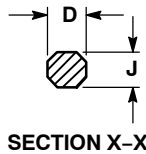
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD  
TAPE & REEL  
AMMO PACK



SECTION X-X

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 14:

1. EMITTER
2. COLLECTOR
3. BASE

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